

VERTICAL FLASH MEMORY CELL WITH BURIED SOURCE RAIL

ABSTRACT OF THE DISCLOSURE

A non-volatile memory cell has been described that includes source and drain regions that are fabricated on different horizontal planes. A floating gate and a control gate are fabricated vertically to control current conducted through the transistor. The control gate is coupled to a word line that is located above the transistor and traverses the memory in a direction perpendicular to the control gate.